



# Thyristor Module

$V_{RRM} = 2 \times 2000 \text{ V}$

$I_{TAV} = 104 \text{ A}$

$V_T = 1.46 \text{ V}$

Phase leg

Part number

**MCC94-20io1B**



Backside: isolated



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

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| Thyristor      |  |  | Ratings                   |      |      |                   |
|----------------|--|--|---------------------------|------|------|-------------------|
| Symbol         | Definition   | Conditions   | min.                      | typ. | max. | Unit              |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$   |                           |      | 2100 | V                 |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}C$   |                           |      | 2000 | V                 |
| $I_{RD}$       | reverse current, drain current                       | $V_{R/D} = 2000 V$   | $T_{VJ} = 25^{\circ}C$    |      | 200  | $\mu A$           |
|                |  | $V_{R/D} = 2000 V$   | $T_{VJ} = 125^{\circ}C$   |      | 15   | mA                |
| $V_T$          | forward voltage drop                                 | $I_T = 150 A$  | $T_{VJ} = 25^{\circ}C$    |      | 1.44 | V                 |
|                |  | $I_T = 300 A$  |                           |      | 1.74 | V                 |
|                |  | $I_T = 150 A$  | $T_{VJ} = 125^{\circ}C$   |      | 1.46 | V                 |
|                |  | $I_T = 300 A$  |                           |      | 1.99 | V                 |
| $I_{TAV}$      | average forward current                              | $T_C = 85^{\circ}C$  | $T_{VJ} = 125^{\circ}C$   |      | 104  | A                 |
| $I_{T(RMS)}$   | RMS forward current                                  | 180° sine  |                           |      | 163  | A                 |
| $V_{T0}$       | threshold voltage                                    | } for power loss calculation only  | $T_{VJ} = 125^{\circ}C$   |      | 0.85 | V                 |
| $r_T$          | slope resistance                                     |  |                           |      | 3.2  | m $\Omega$        |
| $R_{thJC}$     | thermal resistance junction to case                  |  |                           |      | 0.22 | K/W               |
| $R_{thCH}$     | thermal resistance case to heatsink                  |  |                           | 0.2  |      | K/W               |
| $P_{tot}$      | total power dissipation                              |  | $T_C = 25^{\circ}C$       |      | 455  | W                 |
| $I_{TSM}$      | max. forward surge current                           | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 45^{\circ}C$    |      | 1.70 | kA                |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$               |      | 1.84 | kA                |
|                |  | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 125^{\circ}C$   |      | 1.45 | kA                |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$               |      | 1.56 | kA                |
| $I^2t$         | value for fusing                                     | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 45^{\circ}C$    |      | 14.5 | kA <sup>2</sup> s |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$               |      | 14.0 | kA <sup>2</sup> s |
|                |  | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 125^{\circ}C$   |      | 10.4 | kA <sup>2</sup> s |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$               |      | 10.1 | kA <sup>2</sup> s |
| $C_J$          | junction capacitance                                 | $V_R = 700 V \quad f = 1 \text{ MHz}$  | $T_{VJ} = 25^{\circ}C$    |      | 63   | pF                |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30 \mu s$   | $T_C = 125^{\circ}C$      |      | 10   | W                 |
|                |  | $t_p = 300 \mu s$  |                           |      | 5    | W                 |
| $P_{GAV}$      | average gate power dissipation                       |  |                           |      | 0.5  | W                 |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 125^{\circ}C; f = 50 \text{ Hz}$   | repetitive, $I_T = 250 A$ |      | 150  | A/ $\mu s$        |
|                |  | $t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$<br>$I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$                                      | non-repet., $I_T = 104 A$ |      | 500  | A/ $\mu s$        |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$                                     | $T_{VJ} = 125^{\circ}C$   |      | 1000 | V/ $\mu s$        |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$    |      | 1.5  | V                 |
|                |  |  | $T_{VJ} = -40^{\circ}C$   |      | 1.6  | V                 |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$    |      | 150  | mA                |
|                |  |  | $T_{VJ} = -40^{\circ}C$   |      | 200  | mA                |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$  | $T_{VJ} = 125^{\circ}C$   |      | 0.25 | V                 |
| $I_{GD}$       | gate non-trigger current                             |  |                           |      | 10   | mA                |
| $I_L$          | latching current                                     | $t_p = 10 \mu s$   | $T_{VJ} = 25^{\circ}C$    |      | 200  | mA                |
|                |  | $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$   |                           |      |      |                   |
| $I_H$          | holding current                                      | $V_D = 6 V \quad R_{GK} = \infty$  | $T_{VJ} = 25^{\circ}C$    |      | 150  | mA                |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$<br>$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$  | $T_{VJ} = 25^{\circ}C$    |      | 2    | $\mu s$           |
| $t_q$          | turn-off time  | $V_R = 100 V; I_T = 150 A; V = \frac{2}{3} V_{DRM}$<br>$di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$ | $T_{VJ} = 100^{\circ}C$   |      | 185  | $\mu s$           |



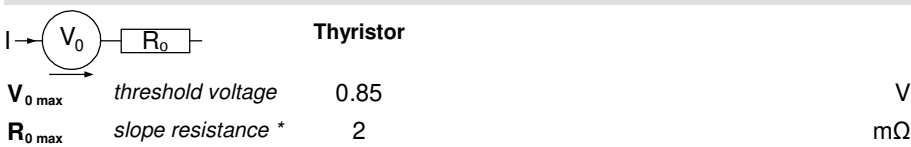
| Package TO-240AA |  |                      |                                     | Ratings |      |      |  |
|------------------|--|----------------------|-------------------------------------|---------|------|------|--|
| Symbol           | Definition   | Conditions           | min.                                | typ.    | max. | Unit |  |
| $I_{RMS}$        | RMS current  | per terminal         |                                     |         | 200  | A    |  |
| $T_{VJ}$         | virtual junction temperature                                 |                      | -40                                 |         | 125  | °C   |  |
| $T_{op}$         | operation temperature  |                      | -40                                 |         | 100  | °C   |  |
| $T_{stg}$        | storage temperature  |                      | -40                                 |         | 125  | °C   |  |
| <b>Weight</b>    |  |                      |                                     |         | 81   | g    |  |
| $M_D$            | mounting torque  |                      | 2.5                                 |         | 4    | Nm   |  |
| $M_T$            | terminal torque  |                      | 2.5                                 |         | 4    | Nm   |  |
| $d_{Spp/App}$    | creepage distance on surface   striking distance through air | terminal to terminal | 13.0                                | 9.7     |      | mm   |  |
| $d_{Spb/Apb}$    |  | terminal to backside | 16.0                                | 16.0    |      | mm   |  |
| $V_{ISOL}$       | isolation voltage  | t = 1 second         |                                     | 4800    |      | V    |  |
|                  |  | t = 1 minute         | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 4000    |      | V    |  |



| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCC94-20io1B    | MCC94-20io1B       | Box           | 36       | 463485   |

| Similar Part   | Package     | Voltage class |
|----------------|-------------|---------------|
| MCNA120P2200TA | TO-240AA-1B | 2200          |

**Equivalent Circuits for Simulation** \* on die level  $T_{VJ} = 125^{\circ}C$





**Outlines TO-240AA**



General tolerance: DIN ISO 2768 class „c“



**Optional accessories for modules**

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 200L (L = Left for pin pair 4/5) } UL 758, style 3751  
 Type ZY 200R (R = Right for pin pair 6/7) }



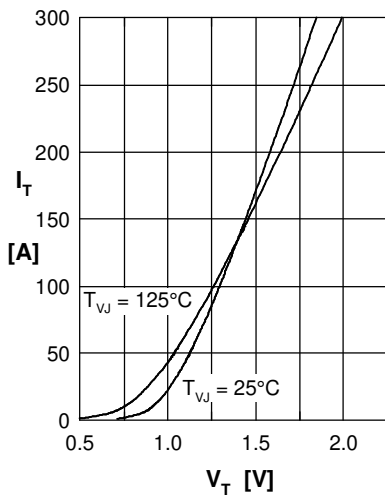
**Thyristor**


Fig. 1 Forward characteristics

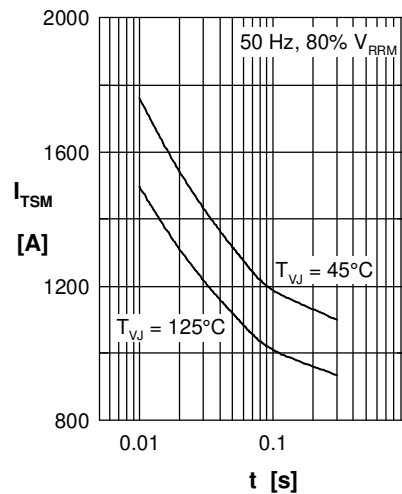
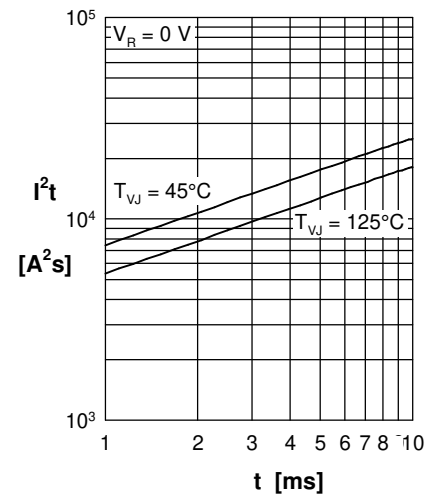
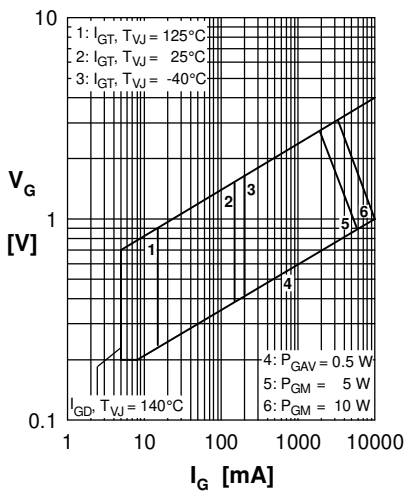

 Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

 Fig. 3  $I^2t$  versus time (1-10 s)


Fig. 4 Gate voltage &amp; gate current

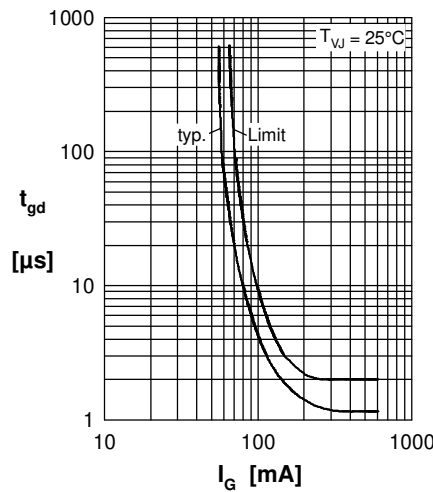
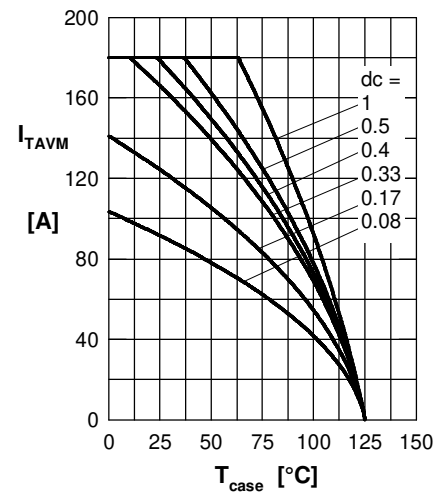

 Fig. 5 Gate controlled delay time  $t_{gd}$ 


Fig. 6 Max. forward current at case temperature

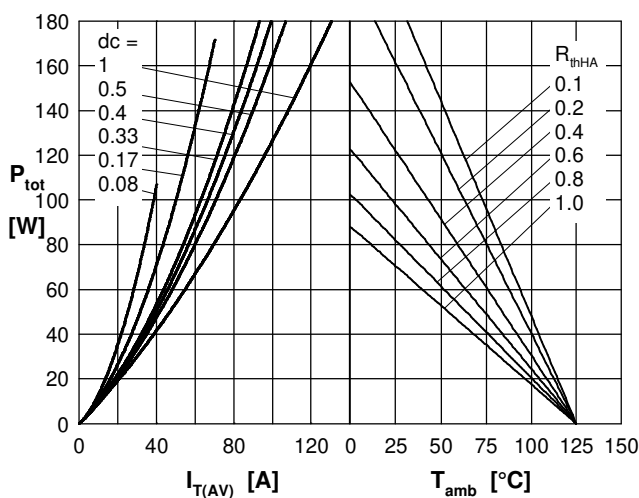
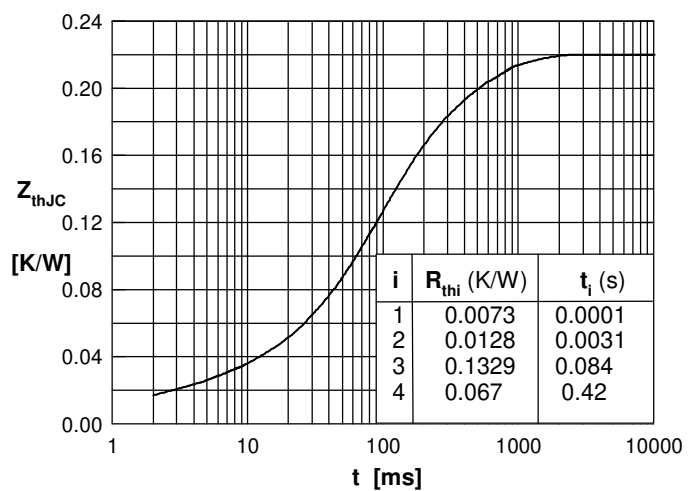

 Fig. 7a Power dissipation versus direct output current  
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case